wherein said precursor is irradiated with an ion beam at least once following said degreasing in said step of forming said ferroelectric film.

43. ~~42.~~ (Currently amended) The method for manufacturing a ferroelectric device according to ~~claim 40~~ claim 42 or claim 41, wherein said ferroelectric film contains a solid solution of $PMN_y$-$PZT_{1-y}$ consisting of a relaxer material PMN comprising any of the compounds $Pb(M_{1/3}N_{2/3})O_3$ (M = Mg, Zn, Co, Ni, Mn; N = Nb, Ta), $Pb(M_{1/2}N_{1/2})O_3$ (M = Sc, Fe, In, Yb, Ho, Lu; N = Nb, Ta), $Pb(M_{1/2}N_{1/2})O_3$ (M = Mg, Cd, Mn, Co; N = W, Re) or $Pb(M_{2/3}N_{1/3})O_3$ (M = Mn, Fe; N = W, Re) or mixed phases of these compounds, and $Pb(Zr_xTi_{1-x})O_3$ (PZT, $0.0 \leq x \leq 1.0$), and is oriented in any of the orientations of a cubic crystal (100), tetragonal crystal (001), rhombohedral crystal (100) or quasi-cubic crystal (100).

42. ~~43.~~ (Previously presented) A method for manufacturing a ferroelectric device, the method comprising:

forming a bottom electrode on a substrate by an ion beam assist method, wherein by irradiating ion beams on the bottom electrode, said bottom electrode has a specific crystal orientation;

forming a ferroelectric film on top of said bottom electrode by an ion beam assist method, wherein by irradiating ion beams on the ferroelectric film, said ferroelectric film has a specific crystal orientation; and

forming a top electrode on top of said ferroelectric film.